

# isc Silicon PNP Power Transistor

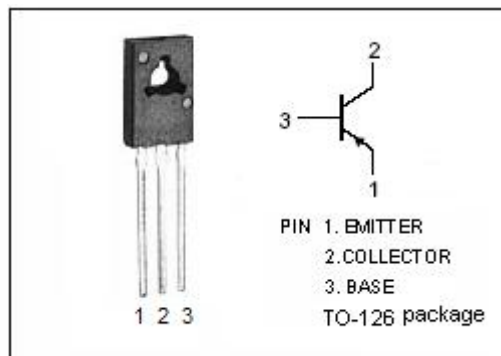
## 2SA794A

### DESCRIPTION

- High Collector-Emitter Breakdown Voltage-  
:  $V_{(BR)CEO} = -120V(\text{Min})$
- Good Linearity of  $h_{FE}$
- Complement to Type 2SC1567A
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

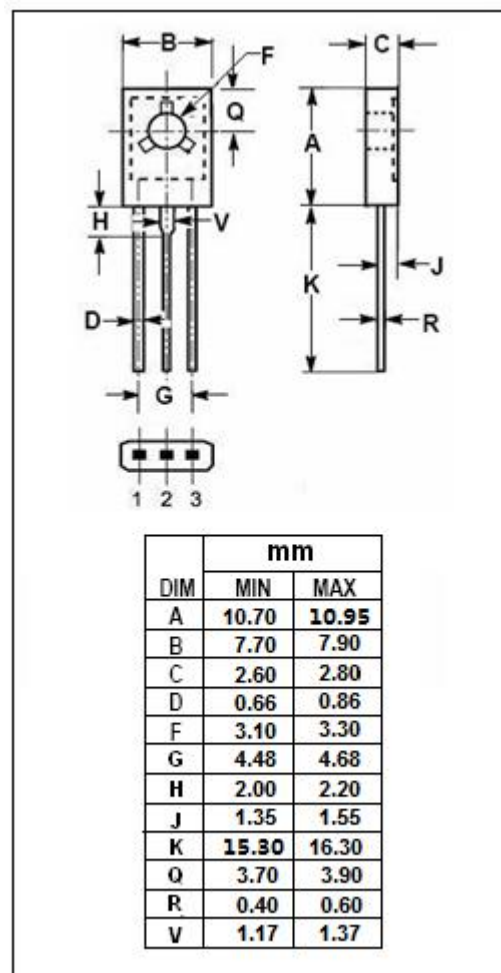
### APPLICATIONS

- Designed for low-frequency high power driver.
- Optimum for the driver stage of low-frequency and 40W to 100W output amplifier.



### ABSOLUTE MAXIMUM RATINGS( $T_a=25^\circ\text{C}$ )

SYMBOL	PARAMETER	VALUE	UNIT
$V_{CBO}$	Collector-Base Voltage	-120	V
$V_{CEO}$	Collector-Emitter Voltage	-120	V
$V_{EBO}$	Emitter-Base Voltage	-5	V
$I_C$	Collector Current-Continuous	-0.5	A
$I_{CP}$	Collector Current-Pulse	-1.0	A
$P_C$	Collector Power Dissipation @ $T_C=25^\circ\text{C}$	10	W
$T_J$	Junction Temperature	150	$^\circ\text{C}$
$T_{stg}$	Storage Temperature Range	-55~150	$^\circ\text{C}$



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## ELECTRICAL CHARACTERISTICS

 $T_C=25^\circ\text{C}$  unless otherwise specified

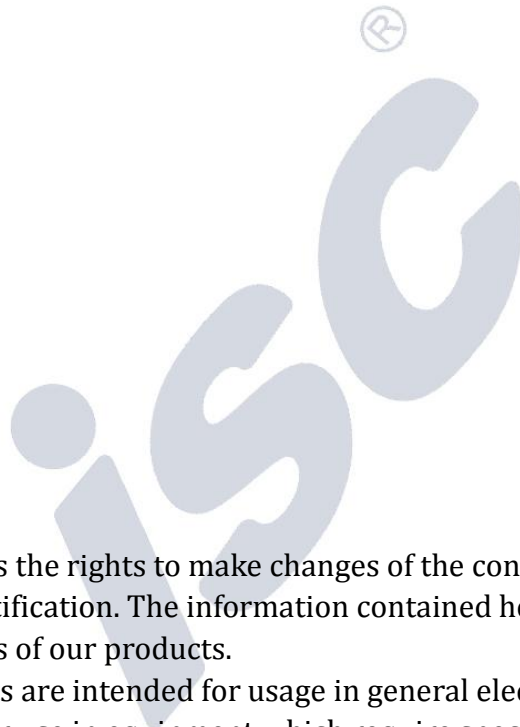
SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{(BR)CEO}$	Collector-Emitter Breakdown Voltage	$I_C = -1\text{mA}$ ; $I_B = 0$	-120			V
$V_{(BR)EBO}$	Emitter-Base Breakdown Voltage	$I_E = -0.1\text{mA}$ ; $I_C = 0$	-5			V
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	$I_C = -500\text{mA}$ ; $I_B = -50\text{mA}$			-0.4	V
$V_{BE(sat)}$	Base-Emitter Saturation Voltage	$I_C = -500\text{mA}$ ; $I_B = -50\text{mA}$			-1.2	V
$I_{CBO}$	Collector Cutoff Current	$V_{CB} = -120\text{V}$ ; $I_E = 0$			-100	$\mu\text{A}$
$I_{EBO}$	Emitter Cutoff Current	$V_{EB} = -5\text{V}$ ; $I_C = 0$			-10	$\mu\text{A}$
$h_{FE-1}$	DC Current Gain	$I_C = -150\text{mA}$ ; $V_{CE} = -10\text{V}$	90		220	
$h_{FE-2}$	DC Current Gain	$I_C = -500\text{mA}$ ; $V_{CE} = -5\text{V}$	50			
$f_T$	Current-Gain—Bandwidth Product	$I_C = -50\text{mA}$ ; $V_{CE} = -10\text{V}$		120		MHz
$C_{OB}$	Output Capacitance	$I_E = 0$ ; $V_{CB} = -100\text{V}$ , $f_{test} = 1\text{MHz}$		20		pF

◆  $h_{FE-1}$  Classifications

Q	R
90-155	130-220

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